



### DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	Package	I <sub>D</sub> T <sub>A</sub> = +25°C
60V	6Ω @ V <sub>GS</sub> = 5V	SOT363	90mA
000	5Ω @ V <sub>GS</sub> = 10V	301303	115mA

### Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### Applications

Load Switch

### Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1KV (HBM)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

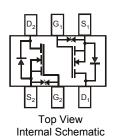
### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe
  (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)





Top View



### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN66D0LDW-7	SOT363	3,000/Tape & Reel

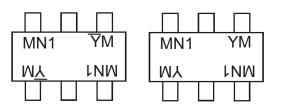
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



ESD PROTECTED TO 1kV

MN1= Product Type Marking Code

 $\frac{YM}{YM} = Date Code Marking for SAT (Shanghai Assembly/ Test site)$   $\frac{YM}{YM} = Date Code Marking for CAT (Chengdu Assembly/ Test site)$   $Y \text{ or } \overline{Y} = Year (ex: A = 2013)$ M = Month (ex: 9 = September)

#### Date Code Key

Date Coue	NEY											
Year	2007	2008	2009	2010	) 201	1 20	)12 2	2013	2014	2015	2016	2017
Code	U	V	W	Х	Y		Z	А	В	С	D	E
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteris	tic	Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	60	V
Gate-Source Voltage (Note 5)	Continuous	V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Continuous Continuous @ +100°C Pulsed	I <sub>D</sub>	115 73 800	mA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation Derating above T <sub>A</sub> = +25°C (Note 5)	PD	250 1.6	mW mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	500	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

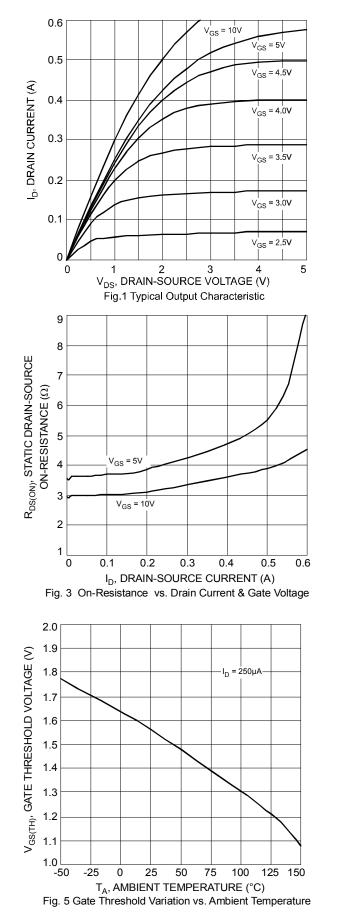
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

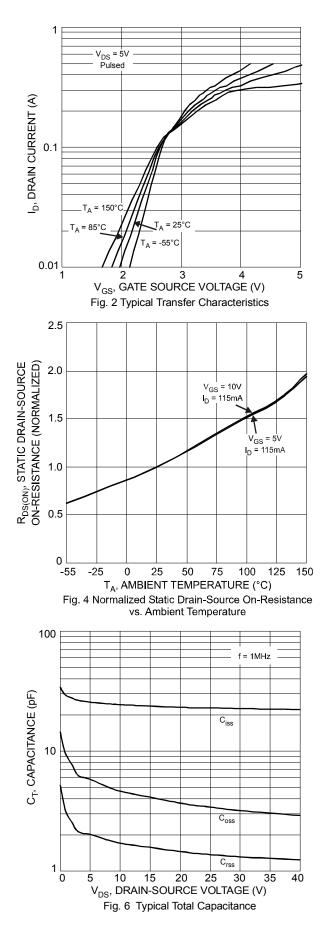
Characteristic		Symbol	Min	Turp	Мах	Unit	Test Condition
Characteristic			IVIIII	Тур	IVIAX	Unit	Test condition
OFF CHARACTERISTICS (Note 6)		1					
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	60	70		V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10µA
Zero Gate Voltage Drain Current	@ T <sub>C</sub> = +25°C @ T <sub>C</sub> = +125°C	I <sub>DSS</sub>	_	—	1.0 500	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage		IGSS	_		±5	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage		V <sub>GS(th)</sub>	1.2		2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T <sub>J</sub> = +25°C		_		6	Ω	V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 0.115A
	@ T <sub>J</sub> = +125°C				5		V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.115A
Forward Transconductance		<b>g</b> fs	80	Vsd	_	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.115
Diode Forward Voltage		V <sub>SD</sub>	_	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
DYNAMIC CHARACTERISTICS				•	•	•	•
Input Capacitance		Ciss	_	23		pF	
Output Capacitance Reverse Transfer Capacitance		Coss	_	3.4	_	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
		Crss	_	1.4		pF	
SWITCHING CHARACTERISTICS		· · ·		•		•	·
Turn-On Delay Time		t <sub>D(ON)</sub>		10		ns	$V_{DD}$ = 30V, $I_D$ = 0.115A, $R_L$ = 150 $\Omega$ ,
Turn-Off Delay Time		t <sub>D(OFF)</sub>		33		ns	$V_{GEN}$ = 10V, $R_{GEN}$ = 25 $\Omega$

 Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.
 Short duration pulse test used to minimize self-heating effect. Notes:

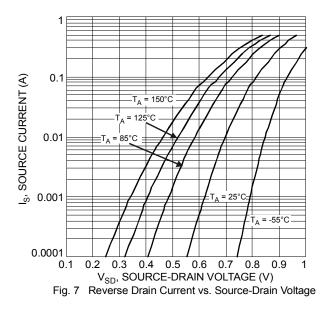
### DMN66D0LDW





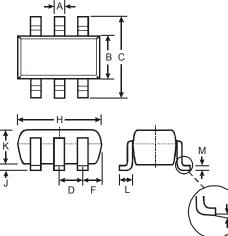






### **Package Outline Dimensions**

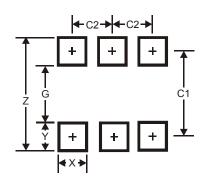
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT363							
Dim	Dim Min						
Α	0.10	0.30					
в	1.15	1.35					
С	2.00	2.20					
D	0.65	Тур					
F	0.40	0.45					
н	1.80	2.20					
J	0	0.10					
ĸ	0.90	1.00					
L	0.25 0.40						
Μ	0.10	0.22					
α	0°	8°					
All Di	All Dimensions in mm						

### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	2.5			
G	1.3			
Х	0.42			
Y	0.6			
C1	1.9			
C2	0.65			



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